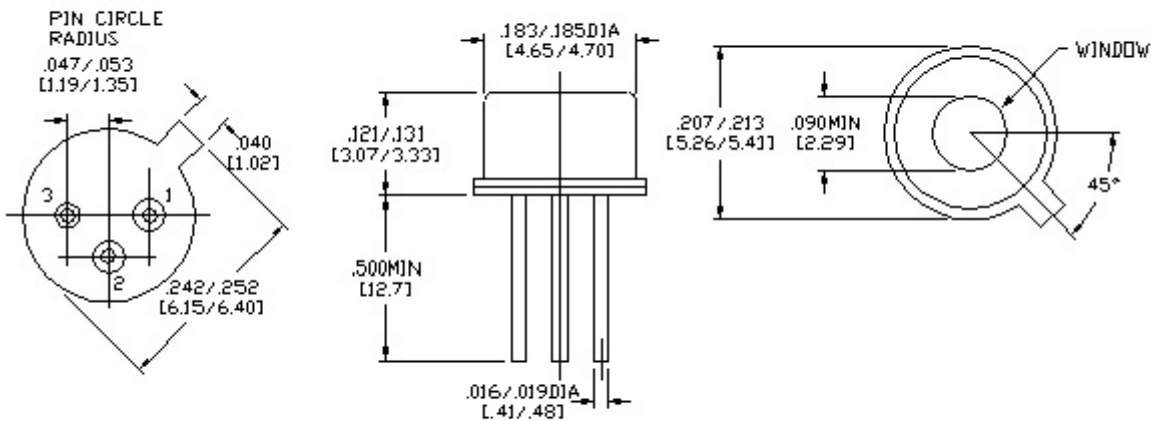


DESCRIPTION

This is a high speed Silicon detector optimized for applications requiring high Responsivity and a fast response time.

FEATURES

- High Responsivity
- High Electrical
- High Reliability/Hermetic Package



ABSOLUTE MAXIMUM RATINGS

- Storage temperature..... -65°C to +150°C
- Case operating temperature..... -55°C to +125°C
- Lead solder temperature..... 260°C, 10 seconds
- Reverse Breakdown Voltage..... 100 Volts

OUTLINE DIMENSIONS

Tolerances are +/-0.005 inches, except as noted
The case is electrically isolated from the pins.
Pin 1. Anode, Pin 2. Cathode, Pin 3. Cathode (Case)

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Capacitance	$V_r = 20\text{ V}, f = 1\text{ MHz}$ C		3.0			pF
Responsivity (50 μm coupled)	$H = 10\ \mu\text{W}, V_r = 5\text{ Volts}$ 50 μm Core, $\lambda = 850\text{ nm}$	R_c	.45	.55		A/W
Dark Current	$V_r = 5\text{ Volts}, H = 0\text{ mW}$	I_d		2	10	nA
Response Time	10%-90%, $V_r = 5\text{ Volts}$ $R_L = 50\ \Omega$	t_r t_f		6.0 6.0	10 10	nsec nsec
Spectral Response		λ	400		1100	nm
Electrical Bandwidth	$V_r = 5\text{ Volts}$	BWE		50		MHz

ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)

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